

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	7016	power near (IC or integrated near circuit)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB; USOCR	2002/03/13 14:11
2	BRS	L2	385	(lateral near pnp near transistor) and (vertical near npn near transistor)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB; USOCR	2002/03/13 14:12
3	BRS	L3	23	L1 and 12	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB; USOCR	2002/03/13 14:13
4	BRS	L4	3	L1 and 12 and (graded near base near region)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB; USOCR	2002/03/13 14:14

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	314	257/500	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB; USOCR	2002/03/1 3 17:52
2	BRS	L2	106	257/525	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB; USOCR	2002/03/1 3 18:05
3	BRS	L3	283	257/575	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB; USOCR	2002/03/1 3 18:22
4	BRS	L4	494	257/653	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB; USOCR	2002/03/1 3 18:24